



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
001/	40mΩ @ V <sub>GS</sub> = 4.5V	5.0A
30V	75mΩ @ V <sub>GS</sub> = 2.5V	3.6A

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

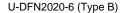
## **Description and Applications**

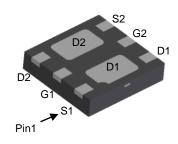
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

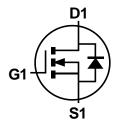
- **Battery Charging**
- **Power Management Functions**
- DC-DC Converters
- Portable Power Adaptors

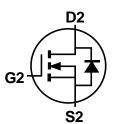
#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)









### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN3055LFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN3055LFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



# **Marking Information**

Site 1



M6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D	 Η		J	K	L	М	Ν	0	Р	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Site 2



M6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	 0	1	2	3	4	5	6	7	8	9

Ī	Week	1-26	27-52	53
ĺ	Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



#### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	30	V	
Gate-Source Voltage		$V_{GSS}$	±12	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			lo	5.0 4.0	Α
Maximum Continuous Body Diode Forward Curren	nt (Note 6)		Is	1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)		IDM	25	Α
Avalanche Current (Note 7) L = 0.1mH		las	11	Α	
Avalanche Energy (Note 7) L = 0.1mH			Eas	6	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	Pn	0.81	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	0.52		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	132	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	R <sub>θ</sub> JA	101	C/VV	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Pp	1.36	W	
Total Fower Dissipation (Note o)	T <sub>A</sub> = +70°C	Pυ	0.87	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Pour	83		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	Reja	60	°C/W	
Thermal Resistance, Junction to Case (Note 6)	_	Rejc	10		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

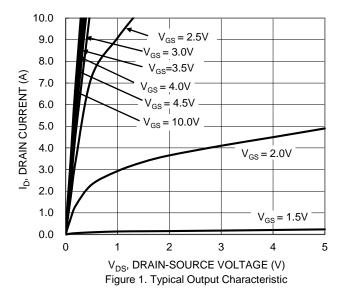
### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				•		•	
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	IDSS	_	_	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	32	40	mΩ	$V_{GS} = 4.5V, I_{D} = 3A$	
Static Drain-Source On-Resistance	RDS(ON)	_	52	75	11112	$V_{GS} = 2.5V, I_{D} = 2A$	
Diode Forward Voltage	V <sub>SD</sub>	_	8.0	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C <sub>iss</sub>		458	_	pF	451/1/	
Output Capacitance	Coss	_	50	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	44	_	pF	1 = 1.0MH2	
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (Vgs = 10V)	Qg	_	11.2	_	nC		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.3	_	nC	\/ 45\/ I- 4A	
Gate-Source Charge	Qgs	_	1.1	_	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4A	
Gate-Drain Charge	Qgd	_	1.8	_	nC		
Turn-On Delay Time	tD(ON)	_	1.8	_	ns		
Turn-On Rise Time	tR	-	2.6	_	ns	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	9.5	_	ns	$R_g = 6\Omega$ , $R_L = 3.75\Omega$	
Turn-Off Fall Time	tF	-	2.1	_	ns	1	
Reverse Recovery Time	trr	_	7.0	_	ns		
Reverse Recovery Charge	Q <sub>RR</sub>	_	1.8	_	nC	$I_F = 3A$ , di/dt = 100A/ $\mu$ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Device mounted on FR-4 substrate PC board, 202 copper, with minimum recommended particles.
Les mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper plate.
I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.





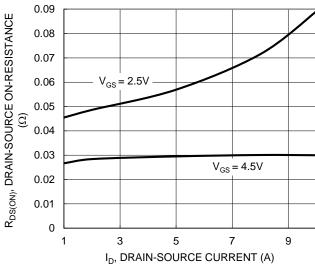


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

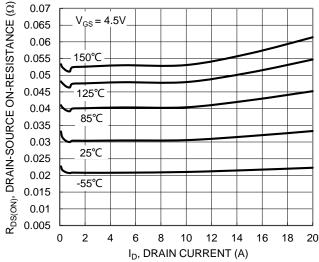


Figure 5 . Typical On-Resistance vs. Drain Current and Temperature

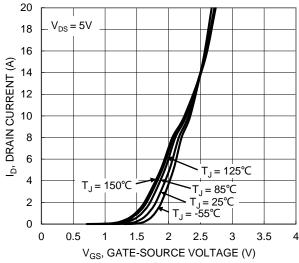


Figure 2. Typical Transfer Characteristic

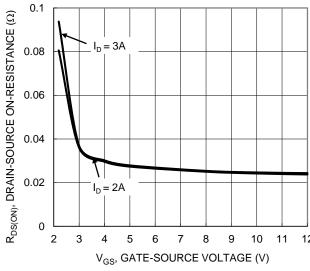


Figure 4 . Typical Transfer Characteristic

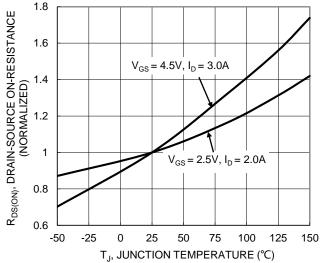


Figure 6. On-Resistance Variation with Temperature



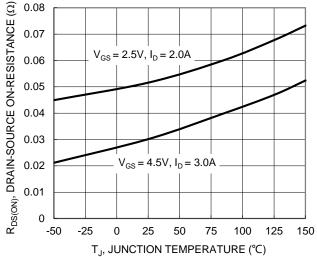


Figure 7. On-Resistance Variation with Temperature

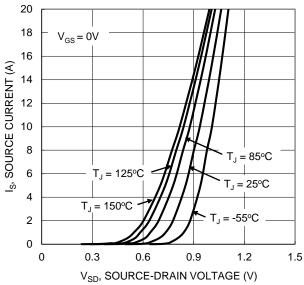


Figure 9. Diode Forward Voltage vs. Current

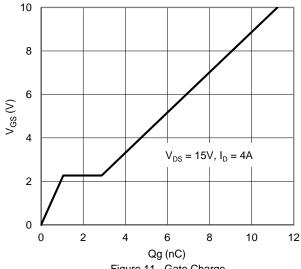


Figure 11. Gate Charge

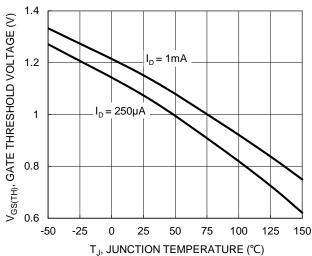
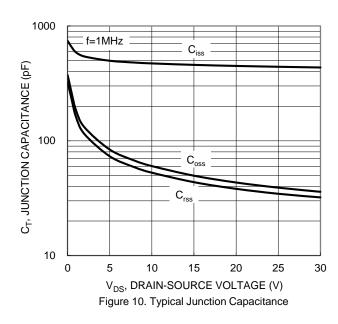


Figure 8. Gate Threshold Variation vs. Junction Temperature



100  $R_{DS(ON)}$  Limited  $P_w = 100 \mu s$ ID, DRAIN CURRENT (A) 10 0.1 T<sub>J(Max)</sub> = 150°C Single Pulse DUT on 1\*MRP Board 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



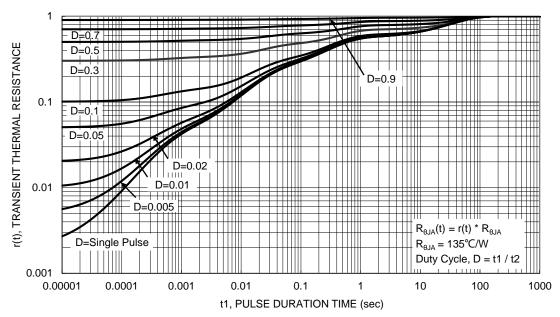


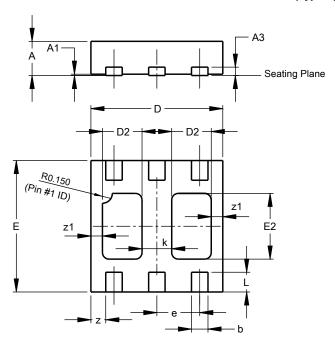
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)

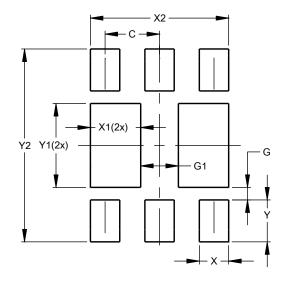


	U-DFN	2020-6							
	(Type B)								
Dim	Min	Min Max Ty							
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	0.50	0.70	0.60						
е	-	-	0.65						
Е	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
Z	-	-	0.225						
z1	-	-	0.175						
All	Dimens	ions in	mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)



Dimensions	Value
	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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